



# STD45NF75

## N-CHANNEL 75V - 0.018 $\Omega$ -40A DPAK STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD45NF75	75 V	<0.024 $\Omega$	40 A(**)

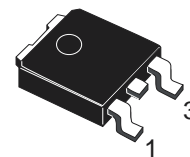
- TYPICAL R<sub>DS(on)</sub> = 0.018  $\Omega$
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- SURFACE-MOUNTING DPAK (TO-252)  
POWER PACKAGE IN TAPE & REEL  
(SUFFIX "T4")

### DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

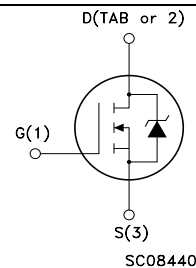
### APPLICATIONS

- HIGH CURRENT, SWITCHING APPLICATIONS



**DPAK  
TO-252**  
(Suffix "T4")

### INTERNAL SCHEMATIC DIAGRAM



### Ordering Information

SALES TYPE	MARKING	PACKAGE	PACKAGING
STD45NF75T4	D45NF75	DPAK	TAPE & REEL

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	75	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 k $\Omega$ )	75	V
V <sub>GS</sub>	Gate- source Voltage	$\pm 20$	V
I <sub>D</sub> (**)	Drain Current (continuous) at T <sub>C</sub> = 25°C	40	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	30	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	160	A
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25°C	100	W
	Derating Factor	0.67	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	20	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	500	mJ
T <sub>stg</sub>	Storage Temperature	-55 to 175	°C
T <sub>j</sub>	Operating Junction Temperature		

(●) Pulse width limited by safe operating area.

(\*\*) Current Limited by Package

(1) I<sub>SD</sub>  $\leq$  40A, di/dt  $\leq$  800A/ $\mu$ s, V<sub>DD</sub>  $\leq$  V<sub>(BR)DSS</sub>, T<sub>j</sub>  $\leq$  T<sub>JMAX</sub>

(2) Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = 20 A, V<sub>DD</sub> = 40V

## STD45NF75

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	1.5	°C/W
Rthj-pcb	Thermal Resistance Junction-pcb	Max	see curve on page 6	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose (for 10 sec. 1.6 mm from case)		275	°C

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

#### OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 µA V <sub>GS</sub> = 0	75			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>C</sub> = 125°C			1 10	µA µA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			±100	nA

#### ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 µA	2		4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 20 A		0.018	0.024	Ω

#### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> = 25 V I <sub>D</sub> = 20 A		50		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		1760 360 140		pF pF pF

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 37\text{ V}$ $I_D = 20\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		15 40		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=60\text{ V}$ $I_D=40\text{ A}$ $V_{GS}= 10\text{ V}$ (see test circuit, Figure 4)		60 13 23	80	nC nC nC

**SWITCHING OFF**

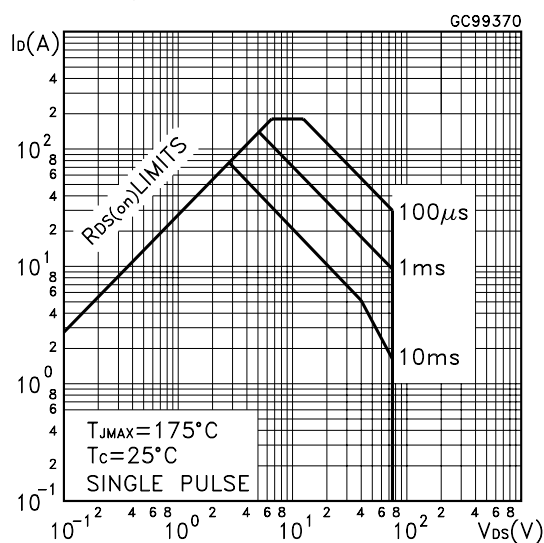
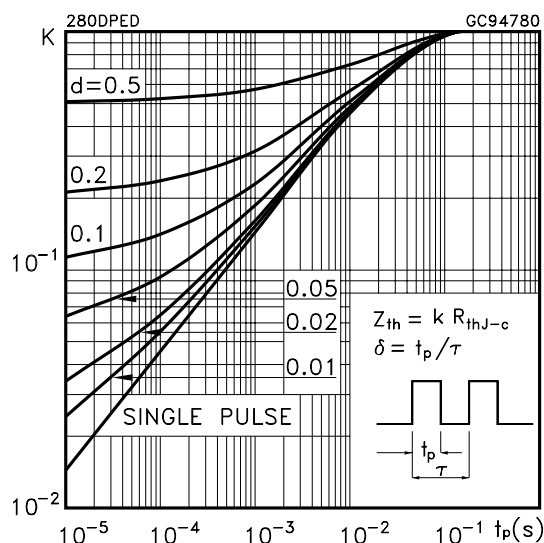
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 37\text{ V}$ $I_D = 20\text{ A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		55 12		ns ns

**SOURCE DRAIN DIODE**

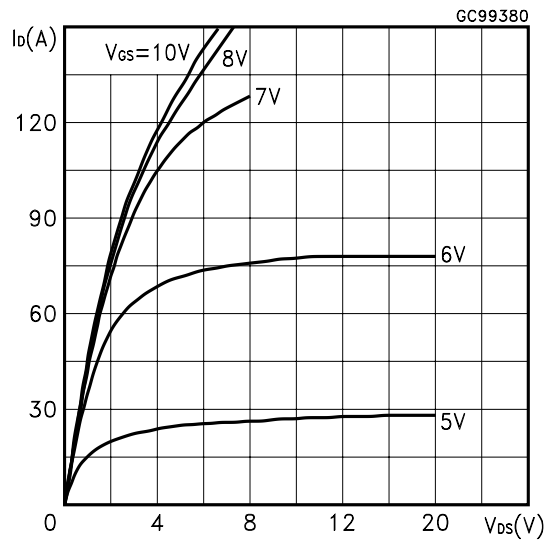
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				40 160	A A
$V_{SD}^(*)$	Forward On Voltage	$I_{SD} = 40\text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 40\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		120 410 7.5		ns nC A

(\*)Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

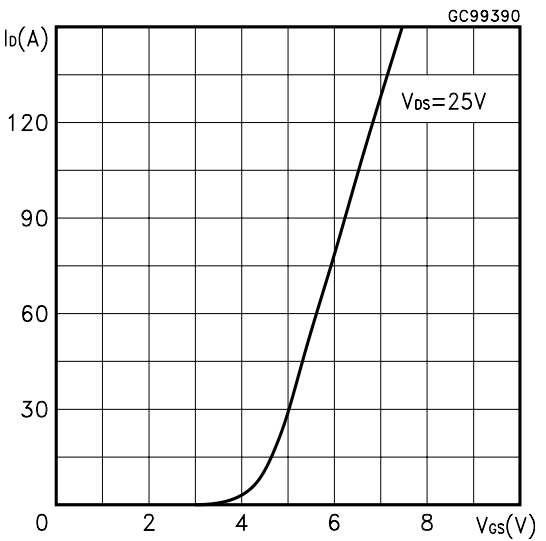
(•)Pulse width limited by safe operating area.

**Safe Operating Area****Thermal Impedance**

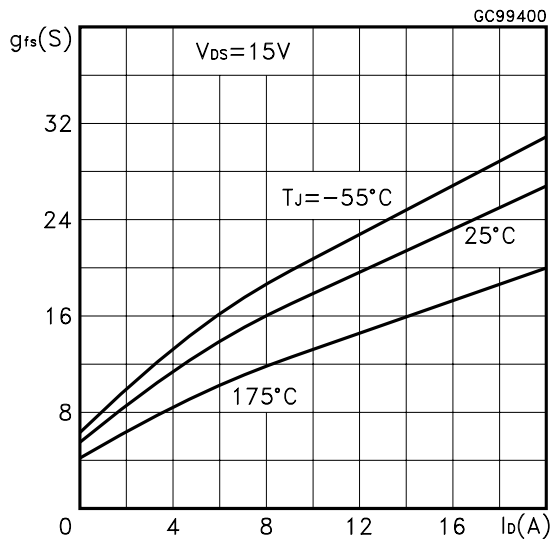
Output Characteristics



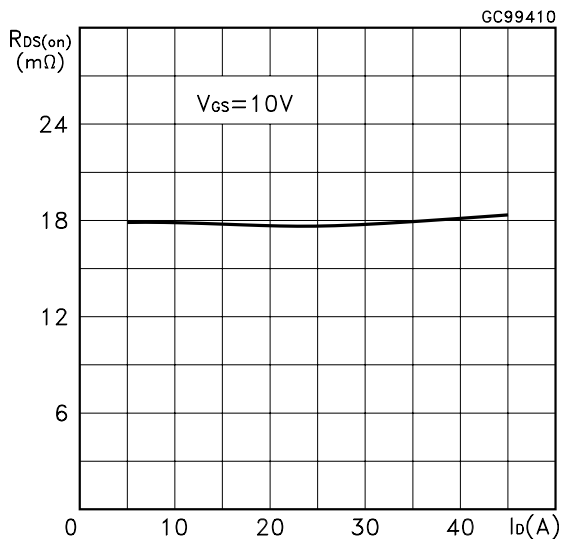
Transfer Characteristics



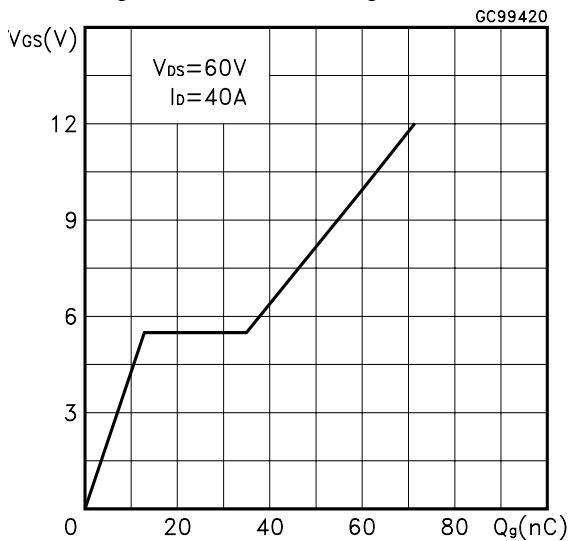
Transconductance



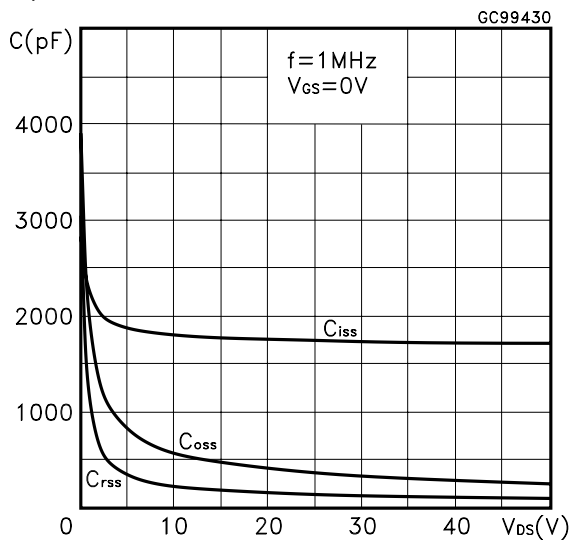
Static Drain-source On Resistance

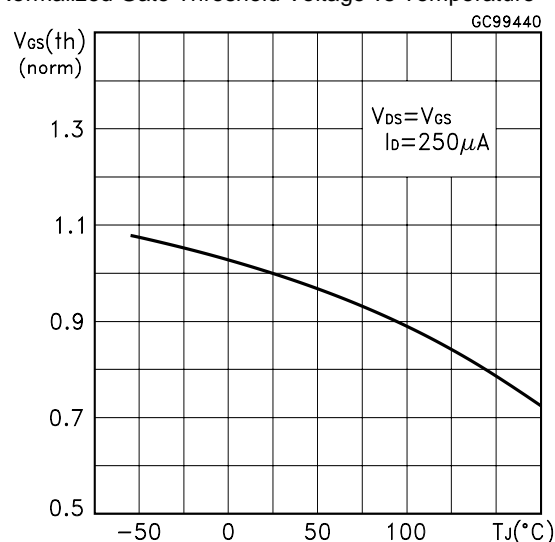
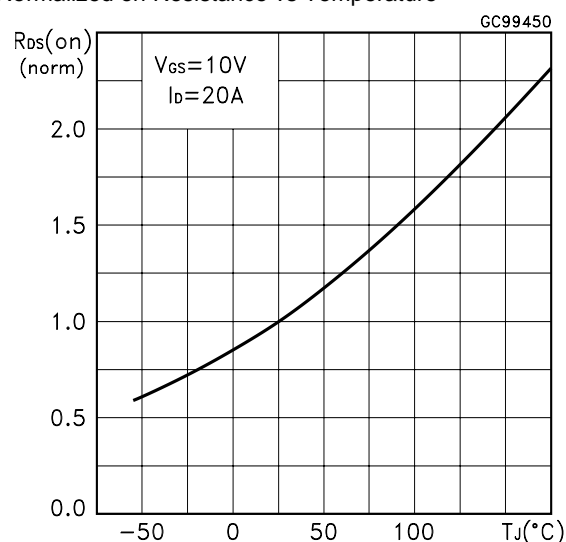
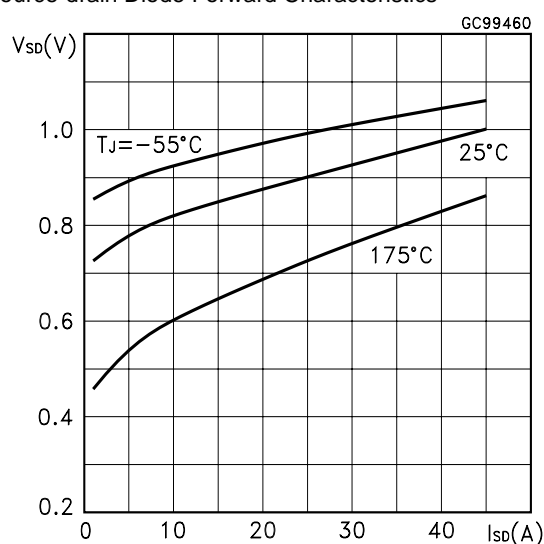
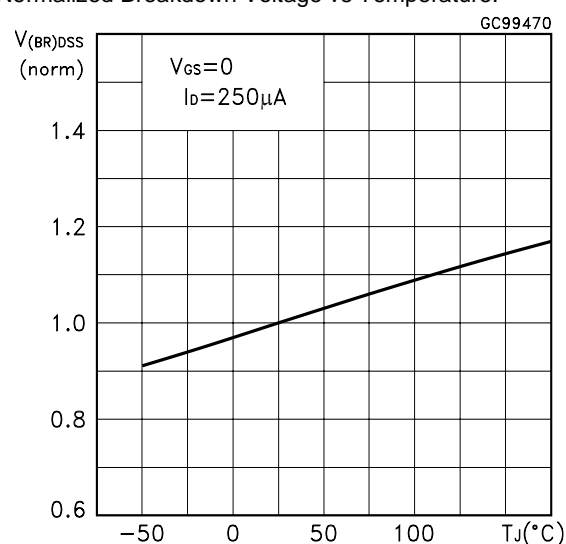
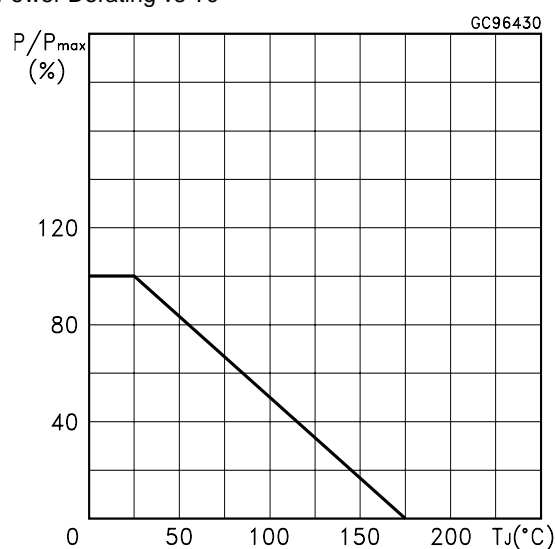
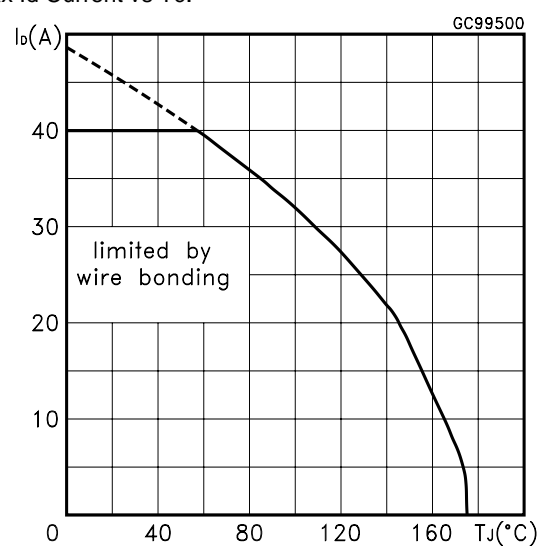


Gate Charge vs Gate-source Voltage



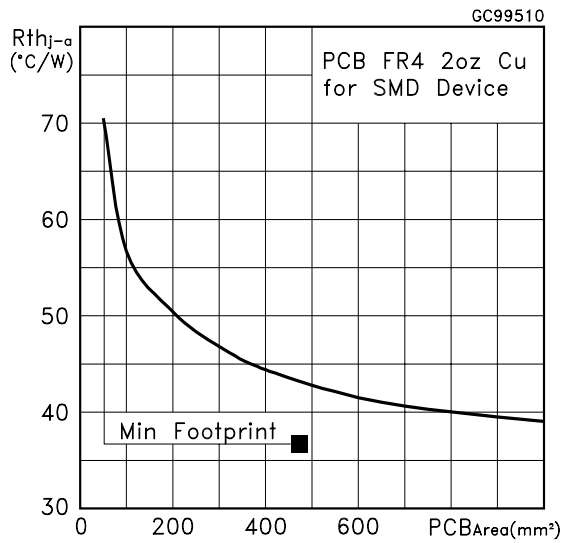
Capacitance Variations



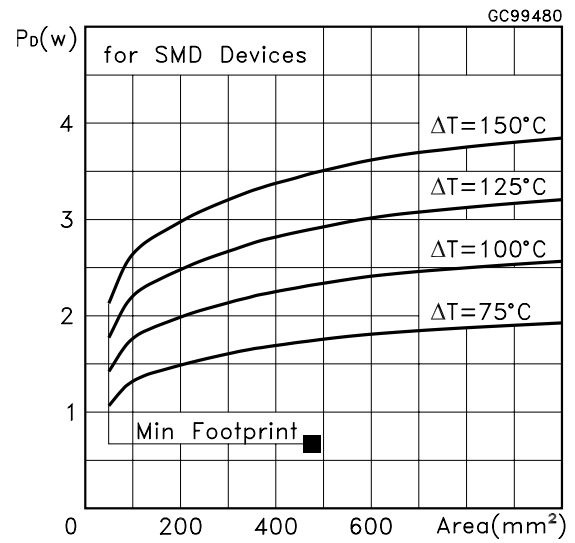
**Normalized Gate Threshold Voltage vs Temperature**

**Normalized on Resistance vs Temperature**

**Source-drain Diode Forward Characteristics**

**Normalized Breakdown Voltage vs Temperature.**

**Power Derating vs Tc**

**Max Id Current vs Tc.**


## STD45NF75

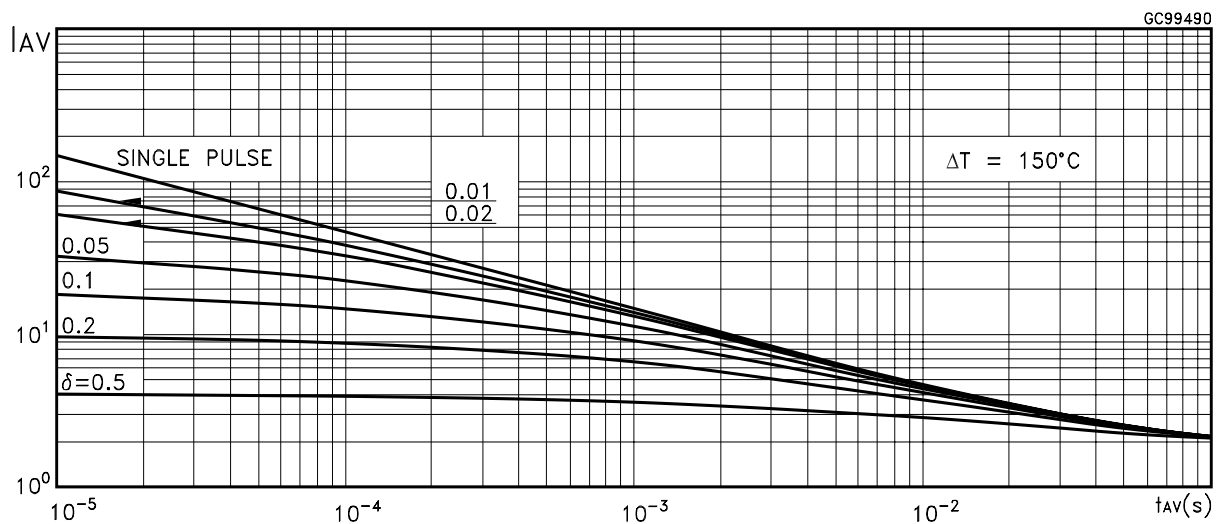
Thermal Resistance Rthj-a vs PCB Copper Area



Max Power Dissipation vs PCB Copper Area



Allowable Iav vs. Time in Avalanche



The previous curve gives the safe operating area for unclamped inductive loads, single pulse or repetitive, under the following conditions:

$$P_{D(AVE)} = 0.5 * (1.3 * BV_{DSS} * I_{AV})$$

$$E_{AS(AR)} = P_{D(AVE)} * t_{AV}$$

Where:

$I_{AV}$  is the Allowable Current in Avalanche

$P_{D(AVE)}$  is the Average Power Dissipation in Avalanche (Single Pulse)

$t_{AV}$  is the Time in Avalanche

To derate above 25 °C, at fixed  $I_{AV}$ , the following equation must be applied:

$$I_{AV} = 2 * (T_{jmax} - T_{CASE}) / (1.3 * BV_{DSS} * Z_{th})$$

Where:

$Z_{th} = K * R_{th}$  is the value coming from Normalized Thermal Response at fixed pulse width equal to  $T_{AV}$ .

## SPICE THERMAL MODEL

Parameter	Node	Value
CTHERM1	7 - 6	$6 * 10^{-4}$
CTHERM2	6 - 5	$8 * 10^{-3}$
CTHERM3	5 - 4	$2 * 10^{-2}$
CTHERM4	4 - 3	$6 * 10^{-2}$
CTHERM5	3 - 2	$9.65 * 10^{-2}$
CTHERM6	2 - 1	$6 * 10^{-1}$
R THERM1	7 - 6	0.045
R THERM2	6 - 5	0.105
R THERM3	5 - 4	0.150
R THERM4	4 - 3	0.225
R THERM5	3 - 2	0.375
R THERM6	2 - 1	0.600

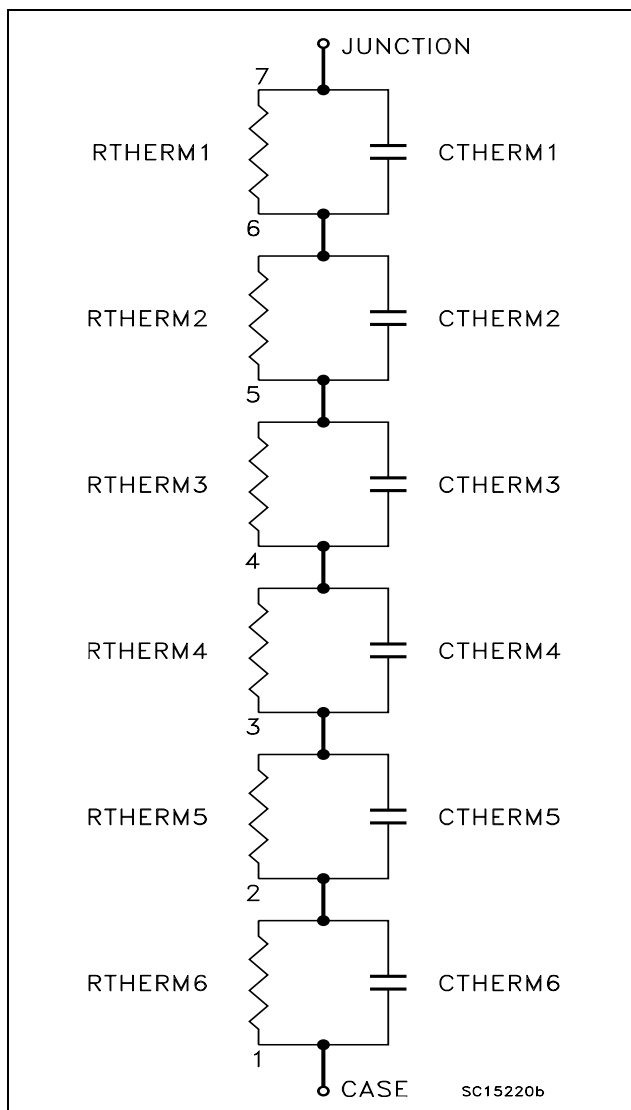


Fig. 1: Unclamped Inductive Load Test Circuit

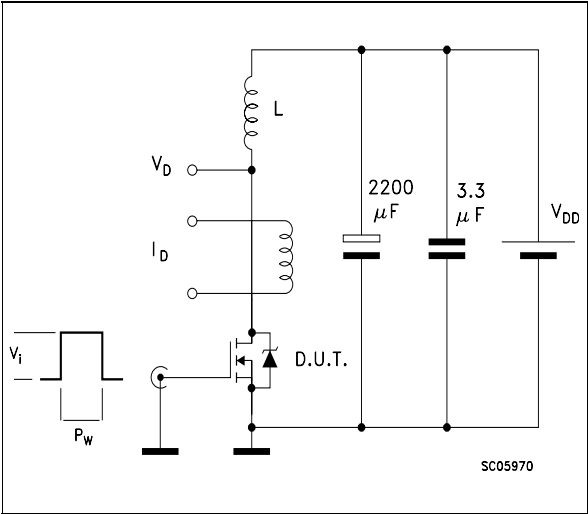


Fig. 2: Unclamped Inductive Waveform

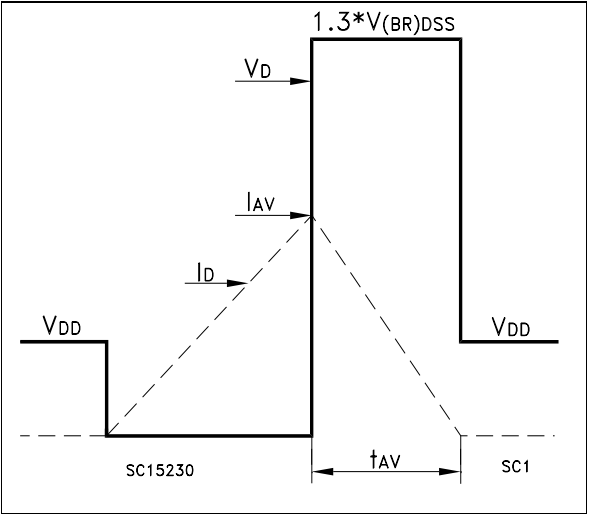


Fig. 3: Switching Times Test Circuits For Resistive Load

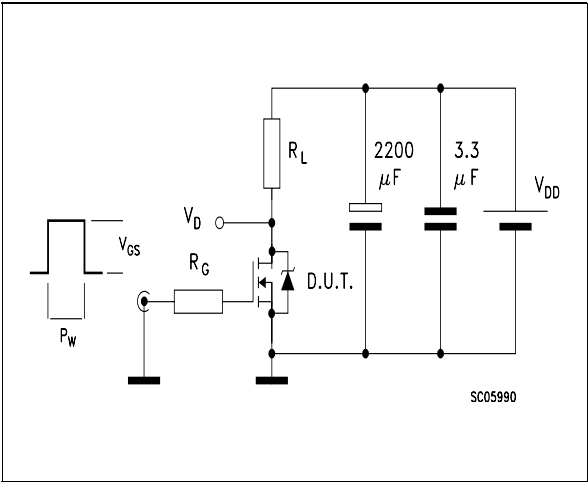


Fig. 3.1: Switching Time Waveform

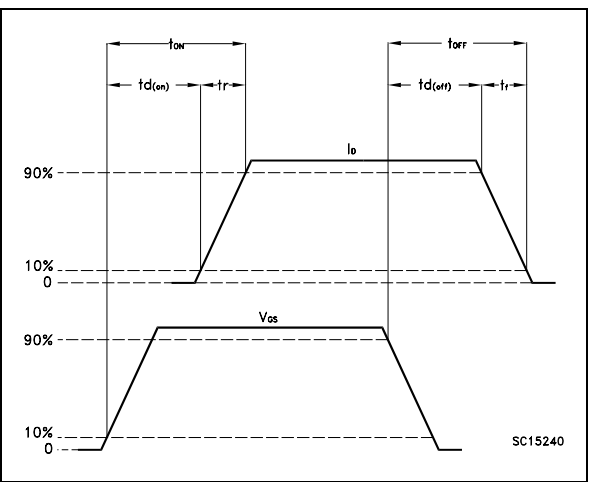


Fig. 4: Gate Charge Test Circuit

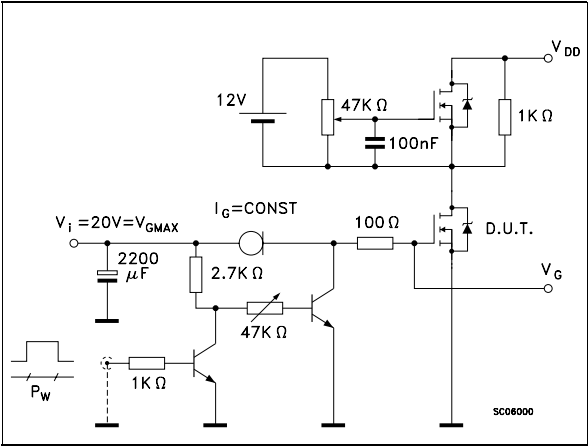
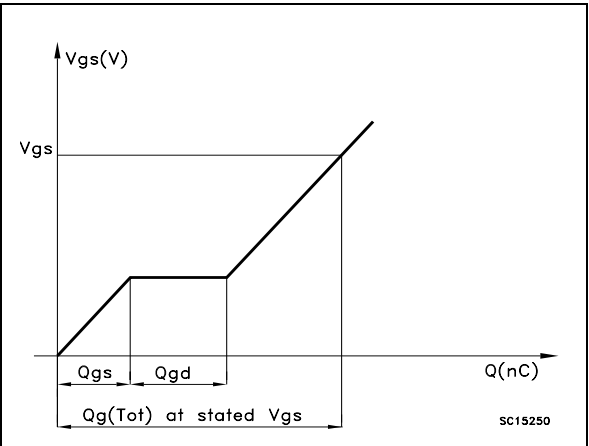
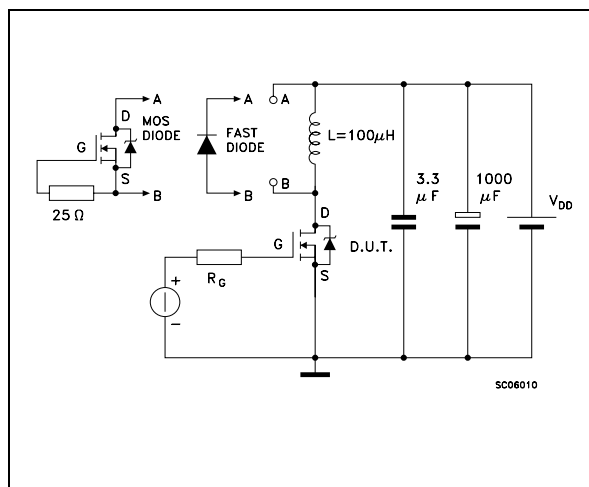
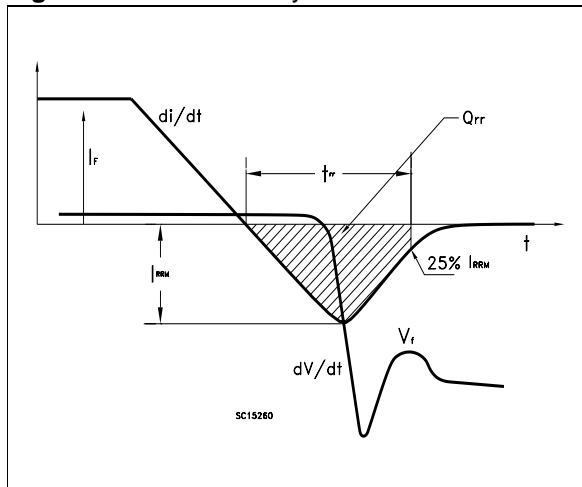


Fig. 4.1: Gate Charge Test Waveform

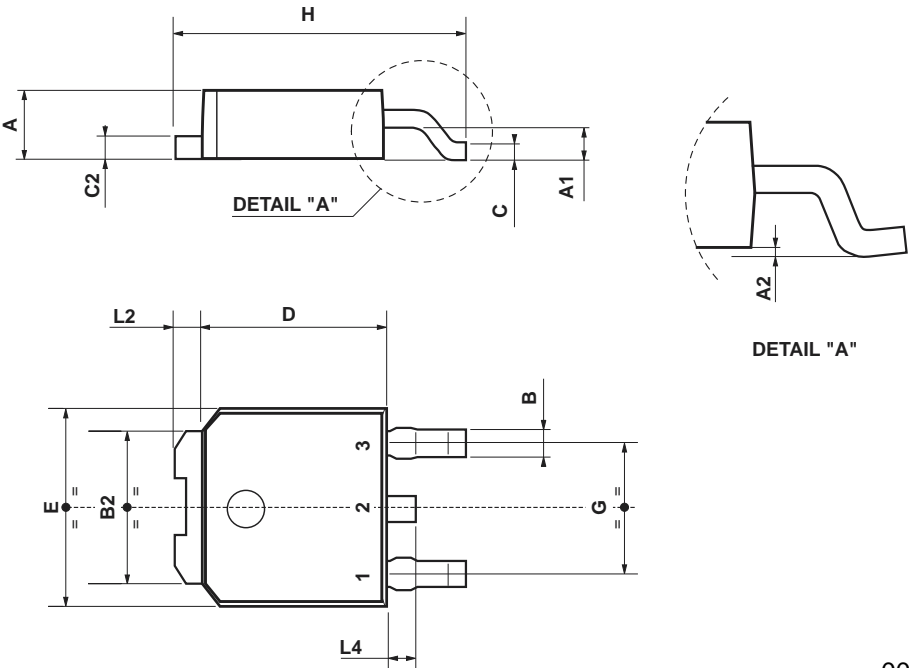




**Fig. 5:** Diode Switching Test Circuit**Fig. 5.1:** Diode Recovery Times Waveform

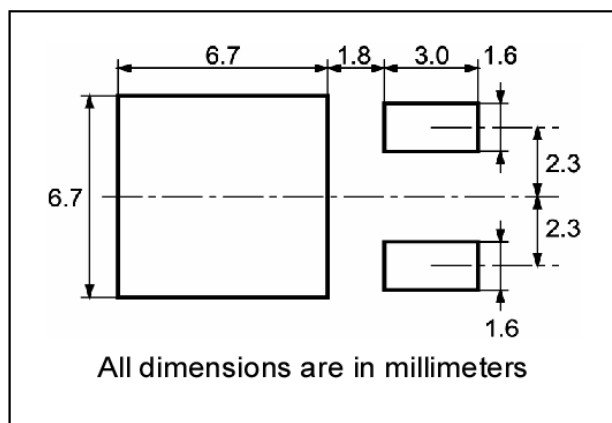
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039

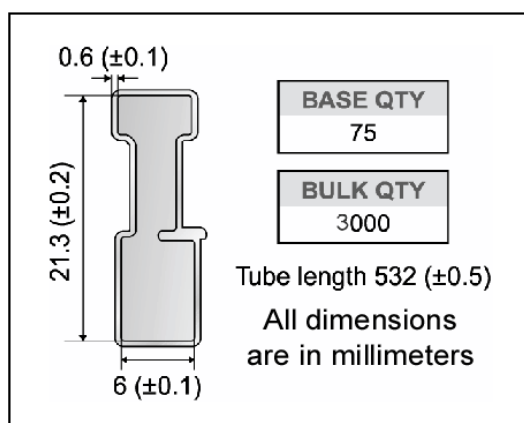


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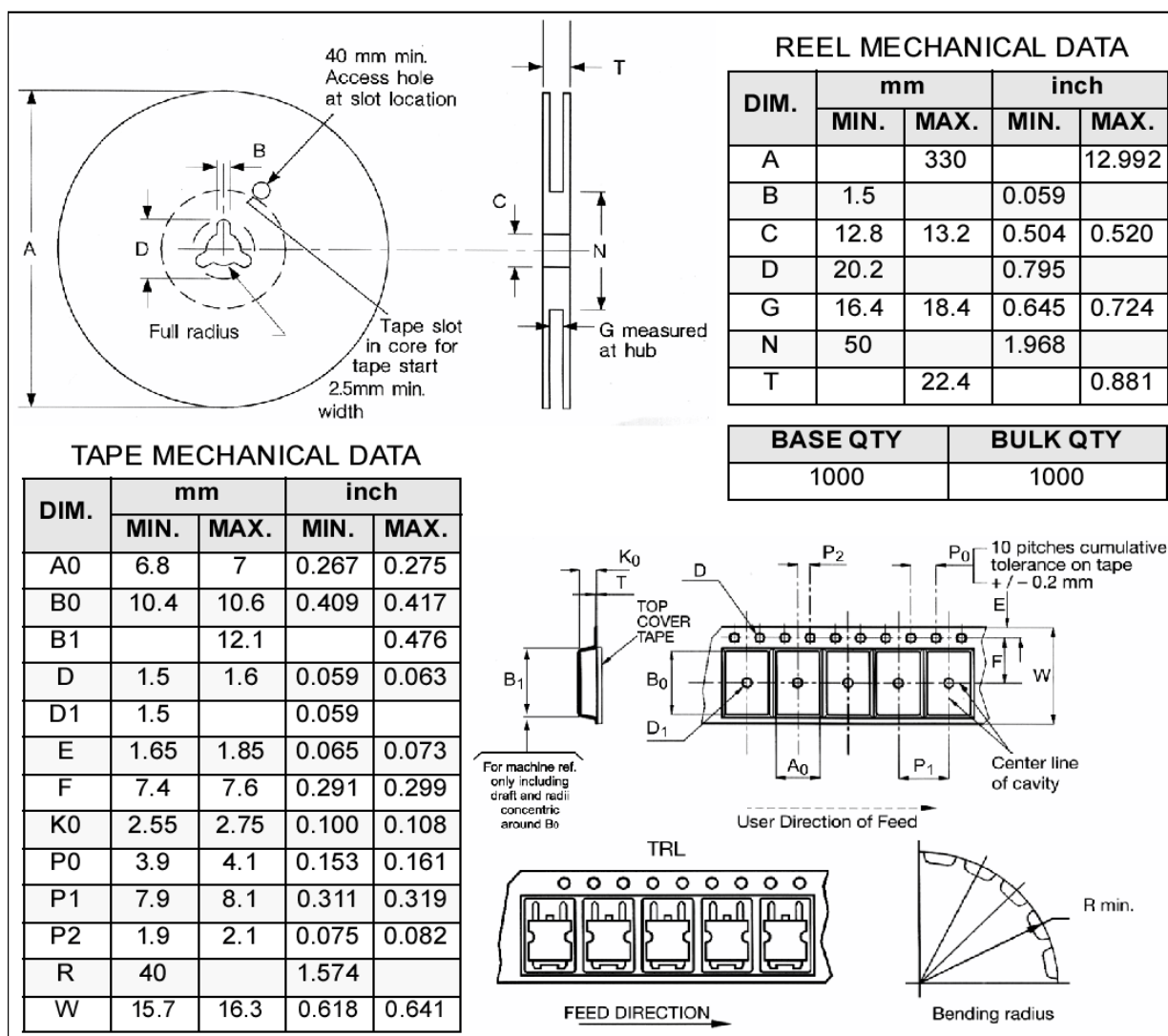
## DPAK FOOTPRINT



## TUBE SHIPMENT (no suffix)\*



## TAPE AND REEL SHIPMENT (suffix "T4")\*



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